

ABSTRACT

A semiconductor device includes a first active pattern on a substrate, a pair of first source/drain patterns on the first active pattern and a first channel pattern between the pair of first source/drain patterns, wherein the first channel pattern includes a plurality of semiconductor patterns that are stacked and spaced apart from each other, a first gate electrode on the first channel pattern, a first gate cutting pattern that is adjacent to the first channel pattern and penetrates the first gate electrode, and a first residual pattern between the first gate cutting pattern and the first channel pattern. The first residual pattern covers an outermost sidewall of at least one semiconductor pattern of the plurality of semiconductor patterns of the first channel pattern. The first gate electrode includes, on an upper portion of the first gate electrode, a first extension that vertically overlaps the first residual pattern.

FIG. 5D